Contents of Schemes and Tables

	Page
Chapter 2	
Scheme 2.1 The preparations of p-C and p-CNT.	30
Chapter 3	
Scheme 3.1 Proposed pathway to form CaF ₂ / <i>a</i> -C nanowires.	40
Chapter 4	
Table 4.1 Summary of reaction conditions and product morphology.	49
Scheme 4.1 Summary of textured graphite formation from the reaction	58
between CaC ₂ and C _x Cl _y . Chapter 5	
Table 5.1 Summary of morphology of silicon products obtained at	69
different reaction temperatures.	
Scheme 5.1 An illustration of formation of textured silicon from SiCl ₄	78
and metal silicides (metal = Mg, Ca).	
Chapter 6	
Table 6.1 The physical properties of the reactants and products.	84
Table 6.2 Summary of standard enthalpy of reaction, reaction temperature	90
and product morphologies.	

List of Figures

		Page
Chapter 1		
Figure 1.1	The crystal structure of graphite.	2
Figure 1.2	The crystal structure of diamond.	3
Figure 1.3	The structure of carbon nanotube.	4
Figure 1.4	The crystal structure of silicon.	7
Chapter 2		
Figure 2.1	XRD of an as-formed raw product prepared at (A) 323 K;(B) 623 K.	20
Figure 2.2	Images of p-C prepared at 623 K. (A) Low and (B) high magnification	21
	SEM; (C) low magnification and (D) high resolution TEM.	
Figure 2.3	TEM images of phase separated p-C and NaF. (A) Low magnification	22
	Image showing NaF crystals pointed by the arrow and (B) high resolution	
	image of NaF nanocrystals selected from the circled area in (A).	
Figure 2.4	Images of p-CNT prepared at 323 K. (A) Low and (B) high magnification	23
	SEM; (C) low and (D) high resolution TEM.	
Figure 2.5	Images of p-CNT prepared at 623 K. (A) Low and (B) high magnification	24
	SEM; (C) low and (D) high resolution TEM.	
Figure 2.6	TGA (heating rate: 5 deg/min from 298 K to 1173 K, air flow rate:	100
	mL/min) of p-CNT prepared at 623 K and annealed at 1173 K	
	under low pressure 1*10 ⁻³ torr. Significant weight loss occurred	
	at 710 K due to oxidation of the carbon. The residual weight is	
	assigned to the unremoved NaF byproduct.	
Figure 2.7	(A) Cross sectional SEM image of AAO after removal of p-CNT	26
	prepared at 623 K showing crystals in the channels. (B) EDS	
	from the circled area in (A).	

Figure 2.8	Nitrogen adsorption-desorption isotherms and BJH pore size	27
	distribution from the desorption branches (insets). (A) p-C	
	(\blacksquare : adsorption branch; \square : desorption branch) and (B) p-CNT	
	(•: adsorption branch; o: desorption branch).	
Figure 2.9	SEM images of (A) low and (B) high magnifications of graphitized	28
	p-CNT; (C) TEM images of graphitized-p-CNT (D) Zoom-in TEM	
	image of the circle area in figure 4C. (E) HRTEM image gotten	
	from the boxed area in figure 4C graphitized at 3073 K.	
Figure 2.10	Raman spectra of p-CNT (lower) prepared at 623 K and	29
	graphited-p-CNT (upper) graphited at 3073 K.	
Chapter 3		
Figure 3.1	(A) SEM (low magnification), (B) SEM (high magnification)	37
	and (C) EDS of CaF ₂ /a-C nanowires prepared at 973 K;	
	(D) SEM (low magnification), (E) SEM (high magnification)	
	and (F) EDS of MgF ₂ /a-C nanowires prepared at 1138 K.	
Figure 3.2	XRD patterns of the reactant CaC ₂ and the product CaF ₂	38
	grown at temperatures 923 – 1273 K for 4 h.	
Figure 3.3	(A) TEM (low magnification) and SAED (inset), and (B) HRTEM	39
	and enlarged view (inset) of a CaF ₂ /a-C nanowire prepared at 973 K;	
	(C) TEM (low magnification) and SAED (inset), and (D) HRTEM	
	and enlarged view (inset) of a MgF ₂ /a-C nanowire prepared at 1138 K.	
Figure 3.4	HRTEM image of the end of a CaF ₂ /a-C nanowire grown	41
	at 973 K for 12 h.	
Figure 3.5	CaF ₂ /a-C nanowires grown at various temperatures for 4 h. 1023 K:	42
	(a) SEM and (b) EDS, 1273 K: (c) SEM and (d) EDS.	
Figure 3.6	Surface models of CaF ₂ . (111) faces of (a) F-rich and (b) Ca-rich;	43

	(100) faces of (c) F-fich and (d) Ca-fich, (e) and (f) two types of	
	(110) faces with equal Ca and F importance.	
Figure 3.7	(a) A sample of CaF ₂ /a-C prepared at 973 K and reacted with	43
	O ₂ at 773 K for 1 h to remove the a-C shell. (b) EDS of the	
	nanowires shown in (a).	
Chapter 4		
Figure 4.1	SEM and EDS graphite/CaCl ₂ nanostructures synthesized from	50
	CaC ₂ and C _x Cl _y . (A) SEM and (B) EDS of the as-prepared product	
	grown at 1023 K from CCl ₄ ; (C) SEM and (D) EDS of the	
	as-prepared product grown at 1123 K from CCl ₄ ; (E) SEM and	
	(F) EDS of the as-prepared product grown at 1223 K from C₅Cl ₆ .	
Figure 4.2	SEM images of graphite products prepared from CaC ₂ and C ₄ Cl ₆	51
	products after the removed of CaCl ₂ . (A) porous carbon, prepared	
	at 1023 K; (B) fibrous carbon, prepared at 1123 K; (C) lamellar	
	carbon, prepared at 1223 K.	
Figure 4.3	SEM images of graphite products prepared from CaC ₂ and C _x Cl _y	52
	at different temperatures.	
Figure 4.4	TEM images of graphite products prepared from CaC_2 and C_xCl_y	52
	at different temperature.	
Figure 4.5	XRD of graphite/ $CaCl_2(H_2O)_x$ product grown from C_4Cl_6 at 1223 K.	53
Figure 4.6	(A) XRD of graphite products grown at 1023 K — 1223 K from	53
	C ₄ Cl ₆ ; (B) Crystal size Lc of the graphite prepared from CaC ₂	
	and C _x Cl _y at different temperatures.	
Figure 4.7	XRD of graphite products grown at 973 K — 1223 K from	54
	CaC_2 and C_xCl_y .	
Figure 4.8	(A) Raman spectra of graphite products grown at 1023 K — 1223 K	55

	from C ₄ Cl ₆ . (B) Crystal size La of the graphite prepared from CaC ₂	
	and C _x Cl _y at different temperatures.	
Figure 4.9	Raman spectra of graphite products grown at 973 K — 1223 K	56
	from CaC_2 and C_xCl_y .	
Figure 4.10	HRTEM and SAED (inset) images of graphite grown from	57
	CaC ₂ and C ₄ Cl ₆ at (A) 1023 K; (B) 1123 K; (C) 1223 K.	
Figure 4.11	HRTEM of a sample prepared from CaC ₂ and C ₄ Cl ₆ at 1023 K,	57
	showing nearly 100 graphite layer.	
Chapter 5		
Figure 5.1	(A) XRD of silicon/MgCl ₂ /MgCl ₂ (H ₂ O) _x product grown at 1123 K.	68
	(B) XRD of silicon/CaCl ₂ (H ₂ O) _x product grown at 1123 K.	
Figure 5.2	XRD of silicon products grown at 1023 K — 1223 K prepared	69
	from SiCl ₄ reacted with (A) Mg ₂ Si;(B) CaSi ₂ .	
Figure 5.3	SEM and EDS silicon/MgCl ₂ and silicon/CaCl ₂ nanostructures	70
	synthesized from SiCl ₄ and Mg ₂ Si, (A) SEM and (B) EDS of	
	the as-prepared product grown at 1123 K; from CaSi ₂ , (C) SEM	
	and (D) EDS of the as-prepared product grown at 1123 K.	
Figure 5.4	SEM images of silicon products prepared from Mg ₂ Si and SiCl ₄ .	71
	(A) Silicon particles, prepared at 1023 K; (B) silicon nanowires,	
	prepared at 1073 K; (C) coral-like silicon, prepared at 1123 K;	
	(D) flake-like silicon, prepared at 1223 K.	
Figure 5.5	SEM images of silicon products prepared from CaSi ₂ and SiCl ₄ .	72
	(A) Porous silicon, prepared at 1023 K; (B) silicon nanowires,	
	prepared at 1073 K; (C) coral-like silicon, prepared at 1123 K;	
	(D) lamellar silicon, prepared at 1223 K.	
Figure 5.6	TEM studies of silicon products prepared from Mg ₂ Si and SiCl ₄ .	73

	particles prepared at 1023 K. (C) – (E) Images of a single silicon	
	nanowire prepared at 1073 K; (C) low magnification, (D) SAED	
	along [-1 1 1] zone axis, and (E) high resolution. (F) – (H) Images	
	of coral-like silicon prepared at 1123 K; (F) low magnification,	
	(G) SAED along [0 1 1] zone axis, and (H) high resolution.	
	(I) – (K) Images of flake-like silicon prepared at 1223 K;	
	(I) low magnification, (J) SAED along [0 1 1] zone axis, and	
	(K) high resolution.	
Figure 5.7	Varied morphology of silicon products prepared from CaSi ₂ and SiCl ₄ .	75
	(A) TEM image and (B) SAED of porous structure prepared at 1023 K;	
	(C) TEM image and (D) SAED taken along the [0 1 1] zone axis of	
	coral-like silicon prepared at 1123 K; (E) TEM image and (F) SAED	
	taken along the [1 -1 -2] zone axis of lamellar silicon prepared at 1223 K;	
	(G) TEM (low magnification) image and (H) SAED taken along the	
	[-1 1 1] zone axis and (I) HRTEM image of a single silicon nanowire	
	prepared at 1073 K.	
Figure 5.8	Raman spectra of the different structure silicon products prepared	76
	from $SiCl_4$ and Mg_2Si at (A) 1023 K, (B) 1073 K, (C) 1123 K,	
	(D) 1223 K; and CaSi $_2$ at (E) 1023 K, (F) 1073 K, (G) 1123 K,	
	(H) 1223 K.	
Chapter 6		
Figure 6.1	SEM images of products prepared from Mg and C ₄ Cl ₆ . (A) coral-like	86
	carbon, prepared at 1123 K; (B) core-shell structure, prepared at 1173 K;	
	(C) carbon tubes, prepared at 1223 K.	

(A) Low magnification and (B) SAED images of clustered silicon

87

Figure 6.2 SEM and EDS Carbon/NaF nanostructures synthesized from Na and

	C ₆ F ₆ . (A) SEM and (B) EDS of the as-prepared product grown at 423 K;	
	Images of carbon nanotubes after removing NaF. (C) Low and (D) high	
	magnification SEM.	
Figure 6.3	SEM images of products prepared from CaC ₂ and Br ₂ . (A) Low and	88
	(B) high magnification particle-like carbon, prepared at 1023 K;	
	(C) Low and (D) high magnification lamellar structure,	
	prepared at 1223 K.	
Figure 6.4	SEM images of products prepared from CaC ₂ and I ₂ . (A) Low and	88
	(B) high magnification particle-like carbon, prepared at 1023 K;	
	(C) Low and (D) high magnification lamellar structure,	
	prepared at 1223 K.	
Figure 6.5	Various nanostructures synthesized sculpting by different inorganic	91
	salts assisted via vapor-solid reaction growth.	
	8 =	